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Christoph K. Hohle

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Raluca Tiron, CEA-LETI (France)
Douglas J. Guerrero, Brewer Science, Inc. (Belgium)
- 13 Hardmasks and Underlayer Materials
Ryan Callahan, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Gilles R. Amblard, SAMSUNG Austin Semiconductor LLC (United States)
- 14 Process Integration and Multipatterning
Scott W. Jessen, Texas Instruments Inc. (United States)
Nobuyuki N. Matsuzawa, Panasonic Corporation (Japan)